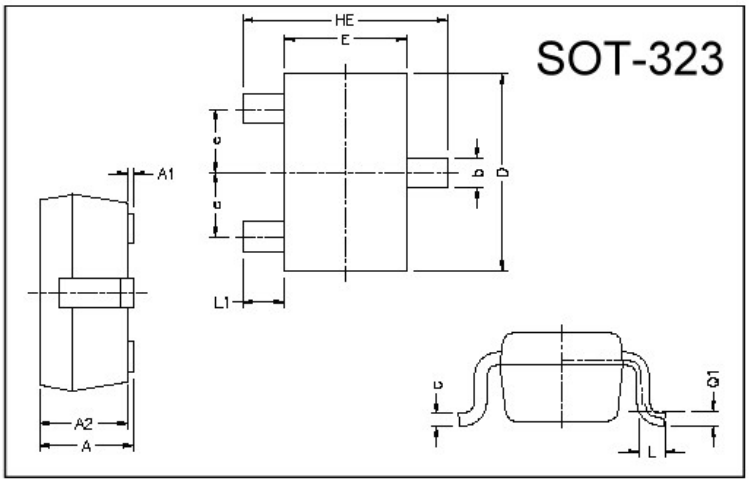
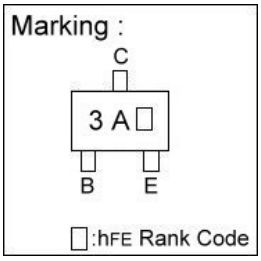
GSMBT9012 PNP EPITAXIAL TRANSISTOR

Description

The GSMBT9012 is designed for use in 1W output amplifier of portable radios in class B push-pull operation.

Package Dimensions





REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25℃

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	℃
Storage Temperature	Tstg	-55 ~ +150	℃
Collector to Base Voltage	VCBO	-40	V
Collector to Emitter Voltage	VCEO	-20	V
Emitter to Base Voltage	VEBO	-5	V
Collector Current	IC	-500	mA
Total Power Dissipation	PD	225	mW

Characteristics at Ta = 25℃

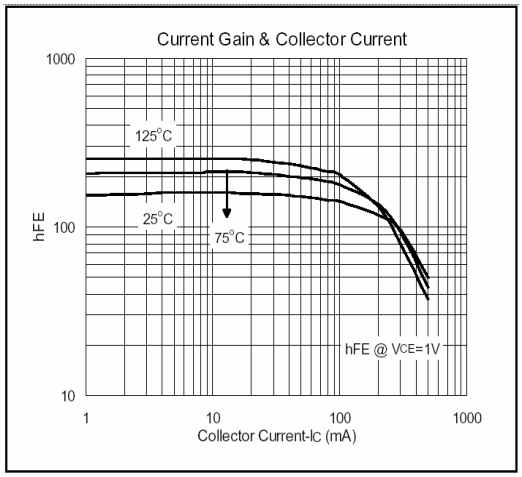
Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	-40	-	-	V	IC=-100uA , IE=0
BVCEO	-20	-	-	V	IC=-1mA, IB=0
BVEBO	-5	-	-	V	IE=-100uA, IC=0
ICBO	-	-	-100	nA	VCB=-25V, IE=0
IEBO	-	-	-100	nA	VEB=-3V, IC=0
*VCE(sat)	-	-	-0.6	V	IC=-500mA, IB=-50mA
*VBE(sat)	-	-	-1.2	V	IC=-500mA, IB=-50mA
*VBE(on)	-	-	-0.9	V	VCE=-1V, IC=-10mA
*hFE1	112	180	300		VCE=-1V, IC=-50mA
*hFE2	40	-	-		VCE=-1V, IC=-500mA
fT	100	-	-	MHz	VCE=-1V, IC=-10mA, f=100MHz
Cob	-	-	8	pF	VCB=-10V, f=1MHz

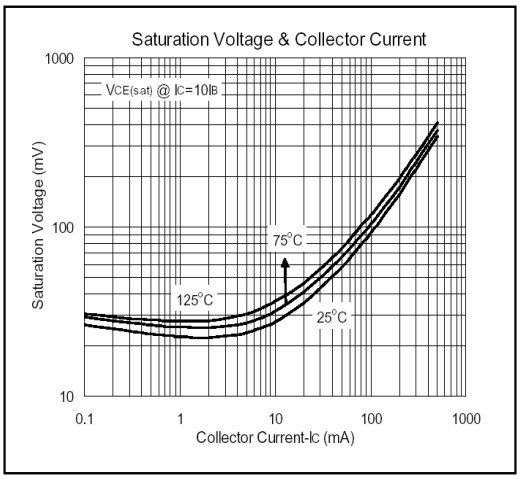
*** Pulse Test: Pulse Width≦380μs, Duty Cycle≦2%**

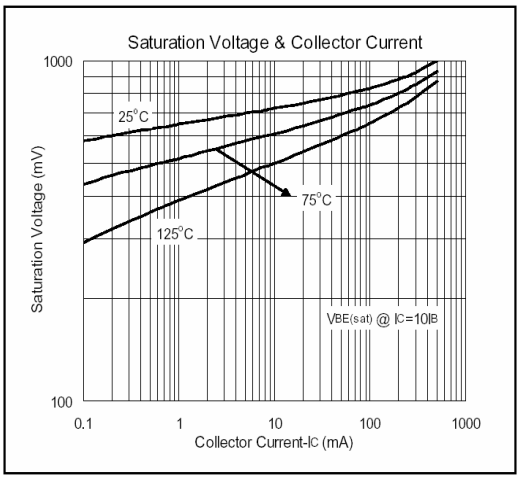
Classification Of hFE1

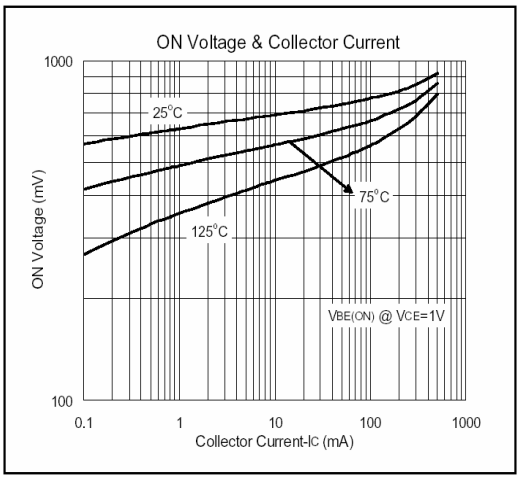
Rank	A3G	A3H	A3L
Range	112 - 166	144 - 202	176 - 300

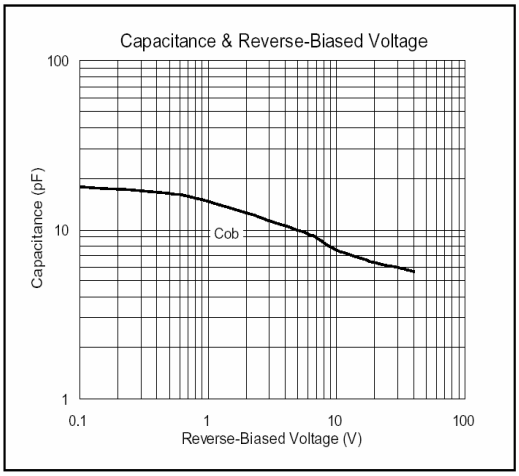
Characteristics Curve

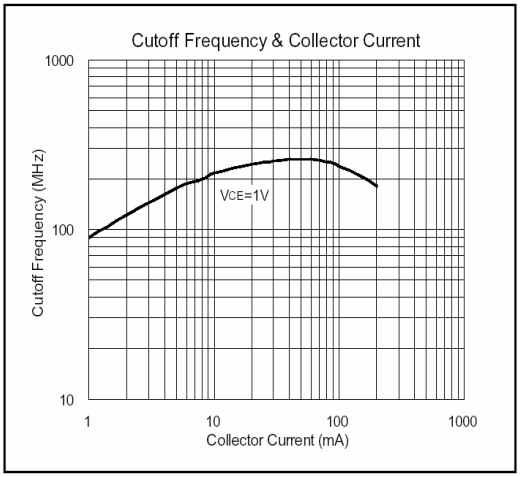












Head Office And Factory:
- **Taiwan**: No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
  TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China**: (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
  TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165